# Accelerated Discovery of Vanadium Oxide Compositions: A WGAN-VAE Framework for Materials Design

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# Abstract

The discovery of novel materials with tailored electronic properties is crucial for advancing modern device technologies, yet traditional approaches rely on time-consuming empirical methods. We present an inverse design framework combining enhanced Wasserstein Generative Adversarial Network (WGAN) with specialized Variational Autoencoder (VAE) to accelerate stable vanadium oxide (V-O) discovery for electronic applications. Our framework introduces a WGAN architecture with integrated stability constraints and formation energy predictions, plus a refined VAE utilizing voxel-based representation that captures atomic positions and lattice parameters while maintaining chemical validity. Applying this framework, we generated 451 unique V-O compositions, with 91 structures identified as stable and 44 as metastable under rigorous thermodynamic criteria, including novel V2O3 configurations below the Materials Project convex hull. Electronic structure analysis using spin-polarized DFT+U calculations revealed distinct electronic behaviors, including promising half-metallic characteristics for spintronics and quantum computing applications. Our approach achieves approximately 20% stability rate under strict criteria compared to previous benchmarks, demonstrating its effectiveness for accelerated materials discovery.

*Keywords:* Inverse design, machine learning, vanadium oxides, WGAN, materials discovery, electronic properties, DFT+U calculations.

# 1. Introduction

The discovery and development of novel materials are pivotal for advancing modern electronic technologies [1], particularly in applications such as semiconductors, memories, batteries, and photovoltaics [2]. Among various material systems, vanadium oxides (V-O) have emerged as particularly promising candidates due to their diverse electronic properties, phase transitions, and structural versatility. These materials exhibit remarkable characteristics including metal-insulator transitions, varied oxidation states, and tunable electronic

properties, making them essential for next-generation electronic devices [3]. However, the systematic discovery of new stable V-O compositions with desired properties remains challenging due to the complex relationship between structure and functionality.

Traditionally, materials exploration has relied heavily on chemical intuition and empirical approaches, such as trial-and-error synthesis and high-throughput screening. While these methods have proven successful in identifying some useful materials, they face significant limitations in efficiency, scalability, and their ability to systematically explore the vast chemical space of possible V-O compositions. The growing demand for materials with precisely tailored properties has created an urgent need for more sophisticated approaches to accelerate materials discovery, particularly those enabling inverse design—where desired properties guide the search for optimal material compositions and structures [4].

High-throughput (HTP) computational workflows, leveraging methods such as Density Functional Theory (DFT), have revolutionized materials discovery by enabling the rapid evaluation of potential candidates. For example, Wines et al utilized an HTP workflow to explore two-dimensional materials exhibiting ferroelectricity and Rashba spin splitting [5]. However, these workflows are computationally intensive and often require significant resources to explore even a small fraction of the possible material space.

To address these challenges, global optimization techniques, including genetic algorithms and Bayesian optimization, have emerged as essential tools. These methods provide efficient navigation through vast and complex design spaces, significantly reducing computational overhead [6]. The CALYPSO method [7] utilizes Particle Swarm Optimization to predict stable and metastable crystal structures from scratch. Its integration of symmetrical constraints and diversity enhancements has proven effective in exploring complex configurational spaces for material discovery. Further developments in this area include Bayesian Optimization approaches for identifying optimal nanoporous materials [8], with Yamashita et al. demonstrating efficient crystal structure prediction through reduced trial numbers in systems like NaCl and  $Y_2Co_{17}$  [9].

Evolutionary algorithms have shown particular promise in crystal structure prediction and material design [10]. Notable advances include the COPEX algorithm by Liu et al. [11], which extends the USPEX evolutionary algorithm through co-evolutionary approaches for complex material systems. The work of Oganov and Glass [12] further demonstrated the evolutionary methods when combined with ab initio calculations, enabling reliable identification of stable and metastable structures across diverse materials without requiring experimental input.

The emergence of machine learning, coupled with comprehensive materials databases such as the Materials Project (MP) [13] and Open Quantum Materials Database (OQMD) [14], has transformed the landscape of inverse materials design. Deep learning techniques [15], including neural networks, have shown remarkable success in diverse applications, such as analyzing high-throughput Transmission Electron Microscope data [16]. More notably, generative models like Variational Autoencoders (VAEs) [17] and Generative Adversarial Networks (GANs) [18], alongside Reinforcement Learning and Invertible Neural Networks, have revolutionized inverse design by enabling the generation of novel materials with tailored properties [19]. The neural network (ResNet18) was used to analyze high-throughput Transmission Electron Microscope (TEM) data for phase determination. Raccuglia et al. demonstrated machine learning's potential for predicting lab experiment outcomes [20], and Pan et al. developed a Reinforcement Learning framework for identifying promising inorganic compounds while maintaining chemical validity constraints. Their model learns chemical guidelines, such as charge and electronegativity neutrality, to generate novel compounds targeting properties like formation energy [21]. The MatDesINNe framework by Fung et al. introduced an inverse design technique utilizing invertible Neural Networks to establish bidirectional mappings between material design parameters and target properties [22].

While generative models have shown promise in capturing and replicating underlying data distributions, recent advances have expanded their utility to classification tasks [23], and transfer learning approaches [24]. These models have become particularly valuable for inverse design, effectively bridging computational modeling and experimental validation [25][26]. Generative models like VAEs are popular, designing molecules by learning continuous representations of existing materials to generate new compounds with desired properties [27]. Noh et al. developed the iMatGen model, which uses VAEs and sampling techniques to represent image-based crystals and generate distinct  $V_x O_y$  compounds [28]. In another work, Boltzmann Generators have been adapted to discover new crystal structures, learning the underlying probability distributions of atomic arrangements in stable crystals [29]. Recent work by Nouira et al. with CrystalGAN generates ternary compositions from binary structures using a vector-based representation [30]. Teng Long et al. have further demonstrated the potential of generative models in materials discovery, proposing the Deep Convolutional GAN model to generate new binary materials with specific properties [31].

Despite these advances, two critical challenges persist in the inverse design of electronic materials. First, current generative models often struggle with the complex structural and chemical constraints inherent in V-O systems, leading to unstable or physically impossible structures. Second, while molecular systems benefit from established representations like SMILES [32], the representation of 3D crystal structures remains a fundamental challenge, particularly for materials with complex electronic properties [33].

To address these challenges, we present two key innovations in this study. We developed an enhanced WGAN-based generative framework specifically optimized for V-O systems. Unlike traditional GANs that suffer from mode collapse and gradient vanishing, our model incorporates stability constraints directly into the generation process. This approach enables robust handling of complex structural and chemical constraints, improved training stability through Wasserstein distance optimization, and the integration of formation energy predictions during material generation. In addition, we developed a refined VAE architecture utilizing voxel-based representation that captures the full complexity of 3D crystal structures. This novel approach effectively encodes both atomic positions and lattice parameters, maintains chemical validity through learned constraints, and creates a continuous, invertible latent space suitable for V-O material generation.

The effectiveness of our integrated approach is demonstrated through extensive validation and discovery. We generated and characterized numerous V-O compositions, including VO<sub>2</sub>, V<sub>2</sub>O<sub>3</sub>, and V<sub>2</sub>O<sub>5</sub>, with particular success in identifying novel stable structures. Most notably, we discovered several V<sub>2</sub>O<sub>3</sub> materials with formation energies lower than those in the Materials Project and OQMD convex hulls. These findings not only validate our methodology but also suggest the existence of previously unknown, thermodynamically favorable V-O phases suitable for electronic applications.

The remainder of this paper is organized as follows: Section 2 details our methodology, in-

cluding the enhanced generative models for encoding tasks and material generation. Section 3 presents our results and comprehensively discusses the generated materials' properties and stability. Finally, we conclude with implications for future materials discovery and potential applications in electronic devices.

# 2. Method

## 2.1. Inverse Design Framework

Inverse design represents a paradigm shift in materials discovery, where the process begins with desired properties and works backward to identify materials that meet these criteria (Fig. 1). This approach contrasts with traditional forward design methods, where materials are first synthesized or simulated, and their properties are subsequently analyzed. Our implementation of this approach consists of three main components: (1) dataset construction and curation, (2) material representation and encoding, and (3) generative modeling for new material discovery.

## 2.2. Data Generation and Curation

To address the limited availability of known vanadium oxide compositions, which are insufficient for training robust machine learning models, we developed a systematic data generation pipeline. Building on prior work [28] that curated 10,981 binary materials from the Materials Project database (excluding structures with excessive unit cells), we implemented



Figure 1: Comparison of traditional trial-and-error materials discovery with property-driven inverse design. (a) In the traditional approach, the material's properties are explored by testing various combinations of atomic compositions, structures, and material spaces, often requiring extensive trial-and-error. (b) The inverse design approach starts with a target property and employs computational models to identify the optimal atomic compositions and structures, streamlining the discovery process and enabling efficient exploration of the materials space. a targeted substitution approach specifically for V-O systems and incorporated DFT calculations to compute the formation energies of the V-O structures. This approach yielded a comprehensive dataset capturing diverse compositional and configurational spaces necessary for training robust machine learning models.

#### 2.3. Crystal Structure Representation

Traditional crystallographic formats like CIF (Crystallographic Information File) pose challenges for machine learning due to their discontinuous and heterogeneous nature. We address this limitation through a voxel-based representation approach that captures both spatial and compositional information. Voxel grids offer a spatially detailed depiction of three-dimensional objects, making them particularly well-suited for capturing the intricate structural characteristics of crystals. This voxelization process captures spatial and compositional information about the crystal structure, providing a more compatible and effective input format for generative models. For a typical binary compound, we utilized a method that defines three distinct voxel grids: two grids to represent the spatial distribution of atomic positions for each of the two constituent elements, and a third grid to encode lattice parameters such as dimensions, lengths, and angles.

#### 2.4. Variational Autoencoder Architecture

We developed an enhanced VAE to encode materials into a continuous latent space that seamlessly integrates chemical composition and structural features. The encoder compresses the high-dimensional input data into a compact latent space, while the decoder reconstructs the original input from these latent representations. This continuous and smooth latent space makes the VAE particularly effective for modeling complex material properties.

In our implementation, the VAE was trained using voxelized crystalline structures as input, enabling the model to capture both atomic and lattice-level information. To further enhance the learning process, we incorporated a novel mechanism for handling residual connections, ensuring robust and accurate representations by mitigating potential issues with data misuse. Specifically, in the decoder, we employed residual connections inspired by ResNet [34], where feature maps from earlier layers were upsampled and combined with those in later layers. This architecture significantly improved the model's capacity to learn hierarchical and nuanced material features.

The training process simultaneously optimized the encoder and decoder networks to minimize the total loss, ensuring the latent space effectively preserved both the structural and chemical characteristics of the input data. The total loss function consisted of two key components: the reconstruction loss, which quantifies how accurately the autoencoder reconstructs input data from latent representations, and the Kullback-Leibler (KL) divergence loss, which regularizes the latent space for smoothness and continuity. The reconstruction loss is formulated as:

$$ReconstructionLoss = \frac{1}{N} \sum_{i=1}^{N} \|x_i - \hat{x}_i\|^2$$
(1)

where  $x_i$  is the input data, and  $\hat{x}_i$  is the reconstructed output from the decoder. The KL divergence encourages the latent variables' distribution to approximate a standard nor- mal distribution. By acting as a regularizer, the KL divergence prevents overfitting to the

training data, promoting smoothness and generalizability of the learned latent space. The KL divergence loss is defined as:

$$KLDivergenceLoss = -\frac{1}{2}\sum_{j=1}^{Z_{size}} \left(1 + \log(\sigma^2) - \mu_j^2 - \sigma_j^2\right)$$
(2)

where  $\mu_j$  and  $\sigma^2_{j}$  are the mean of the j-th latent variable produced by the encoder, respectively. The total loss function, which guides the training of the VAE, combines the reconstruction loss and the KL divergence loss as follows:

## $TotalLoss = ReconstructionLoss + \beta \cdot KLDivergenceLoss$ (3)

Here,  $\beta$  is a scaling factor that controls the trade-off between the reconstruction accuracy and the regularization imposed by the KL divergence. A higher  $\beta$  encourages greater regularization, resulting in a smoother and more structured latent space.

Through this carefully balanced training process, the VAE learns to encode input data into a meaningful and continuous latent space while maintaining the ability to decode it back into its original representation. This reversibility ensures the integrity of the encoded latent representations and provides a powerful framework for material property modeling and design.

In our architecture, the encoder employs 3D convolutional layers with Leaky ReLU activation, batch normalization, and dropout, outputting mean and log variance vectors for reparameterization in the latent space. The decoder mirrors this with 3D transposed convolution layers and residual connections enhanced by custom 3D upsampling, enabling precise and robust reconstruction of input structures. A beta-VAE framework balances reconstruction accuracy and latent space regularization via KL divergence, with KL annealing and learning rate scheduling ensuring stable training. This architecture effectively integrates spatial feature extraction, latent regularization, and reconstruction, making it well-suited for complex lattice design.

#### 2.5. Generating New Materials

Generative adversarial networks (GANs) consist of two competing neural networks: the generator (G) and the discriminator (D), trained simultaneously in an adversarial framework. The generator  $G(z; \theta_G)$  maps random noise z into synthetic data samples G(z), while the discriminator  $D(x; \theta_D)$  evaluates whether a given sample x originates from the real data distribution ( $x \cdot P_{data}$ ) or is generated (x = G(z)). This adversarial setup enables the generator to produce increasingly realistic outputs as training progresses.

The Wasserstein Generative Adversarial Network (WGAN) [35] extends the traditional GAN framework by addressing critical challenges such as unstable training, mode collapse, and vanishing gradients. Instead of a binary discriminator, the Wasserstein GAN (WGAN) employs a "critic" C that assigns a continuous score to measure the realness of samples. WGAN optimizes the Wasserstein distance (also known as Earth Mover's distance) between the real data distribution  $P_{data}$  and the generator's output distribution  $P_G$ , leading to more stable training dynamics and enhanced generative performance. These advancements make WGAN a powerful tool for generating high-quality data, particularly in applications requiring precision and reliability.



Figure 2: Workflow of the inverse design framework for generating and evaluating materials. Selected materials from databases are first represented and encoded into a continuous latent space using a VAE. The encoded crystal structures are then used by a GAN, comprising a generator and a critic, along with a stability prediction model, to generate novel material compositions. Generated materials are reconstructed and evaluated for stability through DFT calculations, verifying their feasibility for practical applications.

As illustrated in Fig. 2, the inverse design process begins with a materials database. These materials are represented in voxel space and subsequently encoded into a latent space using a VAE specially optimized for this task. The VAE extracts essential structural and compositional features from the materials, encoding them into a continuous latent space compatible with WGAN. This structured latent representation ensures that the generator operates within a well-defined space, facilitating the creation of realistic and stable material compositions. The combined use of VAE, WGAN, and CNN provides a robust and scalable framework for the inverse design of materials, accelerating the discovery of novel materials with desirable properties.

The generator in the proposed architecture employs a sequential design that combines dense layers, upsampling, and convolutional layers, further enhanced with batch normalization. The discriminator, aligned with WGAN principles, employs convolutional layers with strides, Leaky ReLU activations, dropout, and L2 regularization to assess the realism of generated samples, ensuring a stable training process and superior convergence. The composite model combines these elements and leverages a dual loss function: the WGAN loss for ensuring image quality and a custom formation energy loss for enforcing properties. This WGAN-based framework enables the generation of high-quality, domain-relevant data with enhanced stability and realistic features.

## 3. Discussion and Results

#### 3.1. Computational Setup and Methodology

The research was conducted using a system equipped with an Intel Core i7 CPU, 8GB of RAM, and an Nvidia 820 GPU. The computational environment was developed using Python 3, employing libraries such as TensorFlow, Keras, and ASE (Atomic Simulation Environment) for materials science operations. To ensure a fair comparison, both GAN and WGAN models were trained under identical conditions for 5,000 iterations.

For stability validation, we performed DFT calculations using the PBE functional [36] and PAW-PBE pseudopotentials [37] for V and O atoms, implemented in the VASP program package [38]. Structural relaxation was performed using the conjugate gradient descent method, with convergence criteria set at  $1.0e^{-5}$  for energy and 0.05 eV/Å for force. Computational efficiency was maintained through the use of relatively sparse reciprocal space meshes with a grid spacing of 0.  $5 \text{\AA}^{-1}$ , combined with a plane-wave cutoff energy of 500 eV. The formation energy was computed as:

$$E_{f} = \frac{E_{V_{x}O_{y}} - (xE_{V} + yE_{O})}{x + y}$$
(4)

where  $E_{V_xO_y}$  represents the total energy of the V-O structure,  $E_V$  and  $E_O$  are the energies of isolated vanadium and oxygen atoms, respectively. Electronic property analysis, including DOS and band structure calculations, was performed using VASP with post-processing through VASPKIT [39].

#### 3.2. Model Performance Analysis

The effectiveness of our VAE implementation is demonstrated in Fig. 3, which shows learning curves for both lattice and site components. The models exhibit rapid initial con-



Figure 3: Learning curves of the proposed VAE model. (a) Lattice VAE and (b) Site VAE show the training (black) and test (red) losses over epochs on a logarithmic scale.

vergence, with the lattice VAE stabilizing around epoch 50 and the site VAE reaching stability near epoch 15. The close alignment between training and test losses indicates minimal overfitting and strong generalization capabilities. These results validate our VAE architecture's ability to learn effective latent representations for both lattice and site structures while maintaining stable, low loss values throughout training.

The comparative analysis between GAN and WGAN architectures, illustrated in Fig. 4, reveals significant differences in training stability. The traditional GAN's generator loss shows considerable fluctuations throughout the training process even after 5000 training epochs, reflecting common challenges such as vanishing gradients and generator-discriminator imbalance. In contrast, our WGAN implementation demonstrates remarkably stable convergence, characterized by a smooth, steady decline in generator loss. This enhanced stability can be attributed to the Wasserstein distance metric and weight clipping techniques, which effectively mitigate mode collapse issues while maintaining consistent gradient flow. The superior training dynamics of WGAN underscore its suitability for generating high-quality materials in inverse design applications.

## 3.3. Generation and Stability Analysis of V-O Compositions

Our WGAN framework successfully generated a diverse set of V-O compositions commonly used in electronic devices: 184 VO<sub>2</sub> compositions, 152 V<sub>2</sub>O<sub>3</sub> compositions, and 115 V<sub>2</sub>O<sub>5</sub> compositions. These structures were generated in latent space and subsequently reconstructed to real space using our trained VAE, enabling comprehensive DFT analysis of their properties.

We established more rigorous stability criteria compared to previous work [28], which considered materials stable at formation energies  $E_{f} \ge 0.5$  eV/atom. Our refined classification defines stability through two key metrics: formation energy and distance to the convex



Figure 4: Generator loss functions for GAN (blue) and WGAN (red) over 5000 training epochs.

hull. We classify a structure as stable when its formation energy is negative and its distance to the convex hull is  $\ge 00 \text{ meV}/\text{atom}$ . Meta-stable structures are defined by negative formation energy and convex hull distance  $\le 500 \text{ meV}/\text{atom}$ . This stricter definition ensures higher confidence in the practical viability of identified structures.

The formation energy distributions across the three compositions, shown in Fig. 5, reveal distinct stability patterns.  $VO_2$  and  $V_2O_3$  compositions demonstrate concentrated stability profiles, suggesting more consistent structural patterns, while  $V_2O_5$  shows a broader distribution, indicating a wider exploration of metastable configurations.

#### 3.4. Analysis of Generated Structures

For VO<sub>2</sub> compositions, our model achieved remarkable success rates: of the 184 generated structures, 124 met the stability criteria from [28], and 119 newly generated materials exhibited negative formation energies. Under our stricter criteria, 56 structures qualified as stable and 25 as meta-stable. Fig. 6 visualizes these formation energies relative to the Materials Project convex hull, demonstrating our model's ability to generate thermodynamically favorable configurations. The V<sub>2</sub>O<sub>3</sub> system yielded particularly significant results. From 152 generated structures, 80 satisfied the original stability criteria [28], with 77 showing negative formation energies. Using our enhanced criteria, 33 structures were classified as stable and 18 as meta-stable. Most notably, as shown in Fig. 7, we identified two V<sub>2</sub>O<sub>3</sub> configurations with formation energies below the Materials Project convex hull, representing potentially new, thermodynamically favorable phases not previously documented.

For V<sub>2</sub>O<sub>5</sub> compositions, we generated 115 structures, with 34 showing negative formation energies. Under our stringent criteria, two structures qualified as stable and one as meta-stable, as illustrated in Fig. 8. The complete distribution of stability metrics across all V-O compositions is summarized in Table 1.



Figure 5: The distribution of formation energies for the generated VO<sub>2</sub>, V<sub>2</sub>O<sub>3</sub>, and V<sub>2</sub>O<sub>5</sub> compositions.



Figure 6: Formation energies of the generated VO<sub>2</sub> compositions.

Table 1: Summary of the generated V-O compositions, including the total number of materials, the number of stable and meta-stable structures.

Materials	Total	Stable in [28]	Negative	Stability	Meta-stability
VO <sub>2</sub>	184	124 (67.4%)	119 (64.7%)	56 (30.4%)	25 (13.5%)
V <sub>2</sub> O <sub>3</sub>	152	80 (52.6%)	77 (50.6%)	33 (21.7%)	18 (11.8%)
$V_2O_5$	115	34 (29.6%)	34 (29.6%)	2 (1.7%)	1 (0.87%)
All Materials	451	238 (52.8%)	230 (51%)	91 (20.2%)	44 (9.75%)

## 3.5. Electronic Property Analysis

To comprehensively evaluate the potential of our generated materials for electronic applications, we conducted detailed electronic structure calculations on the most thermodynamically stable configurations identified for each composition (VO<sub>2</sub>, V<sub>2</sub>O<sub>3</sub>, and V<sub>2</sub>O<sub>5</sub>). Our analysis employed spin-polarized DFT+U calculations with the Hubbard U parameter set to 3.25 eV for the V 3d states [40], following established protocols for accurately describing electron correlations in vanadium oxides.

For the most stable VO<sub>2</sub> structure, our calculations revealed intriguing electronic behavior characterized by strong spin-dependent properties. Figure 9 shows the spin-polarized band structure and density of states (DOS) calculations indicating a marked asymmetry between spin channels. The spin-down channel (red lines) exhibits a substantial indirect bandgap of approximately 2.7 eV, indicating insulating behavior. In contrast, the spin-up channel (blue lines) maintains a nearly metallic character with only a minimal gap, near the Fermi level (set at 0 eV in Vaspkit). This pronounced spin dichotomy manifests clearly in the DOS, where the spin-down states show a distinct gap around the Fermi level while spin-up states maintain finite density. Such electronic structure characteristics strongly suggest half-metallic behavior, where one spin channel provides conduction pathways while the other remains



Figure 7: Formation energies of the generated V<sub>2</sub>O<sub>3</sub> compositions.

insulating. The distinct spin-dependent bandgaps make this material particularly promising for spin-filtered electronics and quantum computing applications, where controlled manipulation of electron spin states is crucial. The generated V<sub>2</sub>O<sub>3</sub> compositions display similarly intriguing electronic properties as shown in Fig. 10. Our most stable V<sub>2</sub>O<sub>3</sub> structure, which has formation energy below the Materials Project convex hull, exhibits electronic characteristics that parallel those of VO<sub>2</sub> but with distinct quantitative differences. The spin-resolved calculations again reveal asymmetric behavior between spin channels, indicative of potential



Figure 8: Formation energies of the generated V<sub>2</sub>O<sub>5</sub> compositions.



Figure 9: Spin-polarized DFT+U band structure (left) and spin-resolved DOS (right) for a triclinic VO<sub>2</sub> phase.



Figure 10: The triclinic  $V_2O_3$  phase is represented with the spin-polarized DFT+U band structure and the spin-resolved DOS.

half-metallic properties. The spin-down channel has a band gap of 3.73 eV wider than the VO<sub>2</sub> structure. The band structure shows complex hybridization between V 3d and O 2p states across a broad energy range that can be important in determining the material's elec-

tronic transport properties and magnetic behavior. These electronic structure calculations provide valuable insights into the potential applications of our generated materials. The half-metallic behavior observed in VO<sub>2</sub> and V<sub>2</sub>O<sub>3</sub> structures suggests promising applications in spintronics and magnetic devices, where spin-polarized current is desirable. For V<sub>2</sub>O<sub>5</sub>, the electronic structure analysis, in Fig. 11, reveals that the spin-polarized calculations are densely packed, highly entangled electronic states near the Fermi level in both spin channels. Unlike VO<sub>2</sub> and V<sub>2</sub>O<sub>3</sub>, we observe no clear spin-selective gap formation, even with the inclusion of the Hubbard U term. The DOS calculations indicate the presence of accessible states at and around the Fermi level for both spin orientations, suggesting that electrons in both spin channels can participate in conduction processes. This electronic structure does not sup- port half-metallic behavior but instead points to a more conventional metallic character with possible weak magnetic ordering. These characteristics make this triclinic V<sub>2</sub>O<sub>5</sub> composition particularly promising for transparent conducting oxides, high-performance electrochromic devices, and energy storage systems where rapid electron transport in both spin channels is advantageous.

The low symmetry of these triclinic structures introduces additional complexity in the band structures, manifesting as non-smooth features and intricate band crossings. This complexity arises from the reduced symmetry of the Brillouin zone and the resulting increase in allowed band mixing. The structural distortions in these materials appear to play a significant role in determining their electronic properties, particularly affecting the bandwidth and band hybridization characteristics. The presence of strong electron correlations, evidenced by the significant impact of the Hubbard U term on the electronic structure, indicates that these materials may exhibit interesting phenomena under external stimuli such as temperature, pressure, or electric fields. This susceptibility to external perturbation could



Figure 11: Spin-polarized DFT+U band structure and spin-resolved DOS for the triclinic V<sub>2</sub>O<sub>5</sub> phase.

be particularly valuable for sensing applications or switchable electronic devices.

# 4. Conclusion

In this study, we present an innovative inverse design framework that uses enhanced generative AI architectures to produce stable vanadium oxide compositions, showing that properly constrained machine learning models can navigate complex chemical spaces and accelerate the discovery of novel functional materials. We develop a WGAN with stability constraints for smoother training and improved generation quality, coupled with a voxel-based VAE to capture atomic positions and lattice parameters while maintaining chemical validity. The framework's effectiveness is demonstrated by generating and characterizing 451 unique V–O compositions, of which 91 are stable under strict criteria and 44 are metastable, surpassing previous benchmarks. Spin-polarized DFT+U calculations confirm that the generated materials exhibit diverse and technologically relevant properties. Notably, several V<sub>2</sub>O<sub>3</sub> configurations have formation energies below the Materials Project convex hull, illustrating the framework's ability to discover materials beyond known phase spaces. The new VO<sub>2</sub> structures show half-metallic behavior with spin-dependent bandgaps, while V<sub>2</sub>O<sub>5</sub> structures exhibit metallic character with unique electronic transport properties.

Beyond vanadium oxides, this framework can be adapted to other materials by adjusting chemical constraints and stability criteria, especially for transition metal oxides. Future advances could integrate additional property predictions into the generative process to target materials with specific electronic, optical, or magnetic features. The newly identified stable structures, particularly the novel V<sub>2</sub>O<sub>3</sub> phases, merit experimental synthesis and characterization. Further optimization of the WGAN architecture could improve generation speed and scalability to larger chemical spaces. By combining artificial intelligence with materials science, this approach establishes a robust methodology for accelerating the identification and development of next-generation electronic materials and quantum technologies.

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